

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	2.8mΩ@10V	180A



合肥矽普半导体

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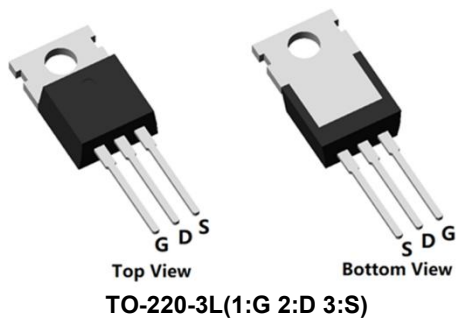
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

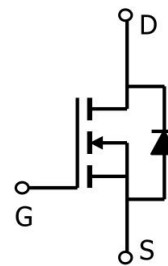
Applications

- Power switching application
- DC-DC Converter
- Power Management

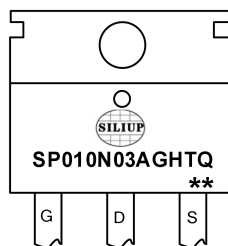
Package



Circuit diagram



Marking



SP010N03AGHTQ :Product code
** :Week code

Order Information

Device	Package	Unit/Tube
SP010N03AGHTQ	TO-220-3L	50

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	180	A
Continuous Drain Current (Tc=100°C)	I_D	120	A
Pulsed Drain Current	I_{DM}	720	A
Single Pulse Avalanche Energy ¹	E_{AS}	1332	mJ
Power Dissipation (Tc=25°C)	P_D	210	W
Power Dissipation (Tc=100°C)	P_D	84	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.60	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

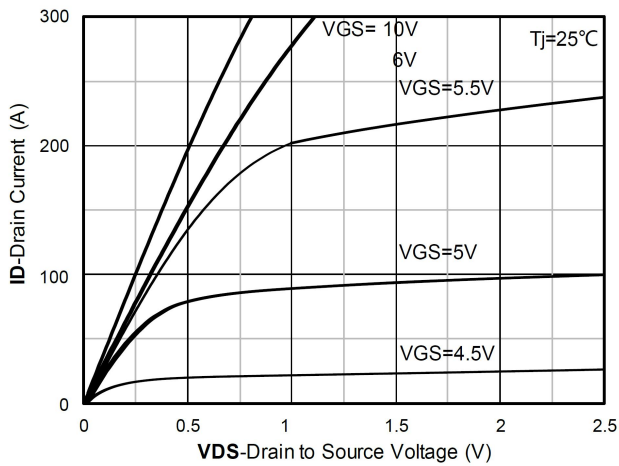
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	ID = 250μA, VGS = 0V	100	-	-	V
Drain Cut-Off Current	IDSS	VDS = 80V, VGS = 0V	-	-	1	μA
Gate Leakage Current	IGSS	VGS = ±20V, VDS = 0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VDS = VGS, ID = 250μA	2.6	3.0	3.4	V
Drain-Source ON Resistance	RDS(ON)	VGS = 10V, ID = 30A	-	2.8	3.5	mΩ
Gate Resistance	RG	VDS = 50V, VGS = 0V, f=1MHz	-	4.2	-	Ω
Dynamic Characteristics						
Input Capacitance	Ciss	VDS = 50V, VGS = 0V, f = 1.0MHz	-	7000	-	pF
Output Capacitance	Coss		-	2580	-	
Reverse Transfer Capacitance	Crss		-	63	-	
Total Gate Charge	Qg	VDS = 50V, VGS = 10V, ID = 100A	-	114	-	nC
Gate-Source Charge	Qgs		-	47	-	
Gate-Drain Charge	Qgd		-	28	-	
Gate Plateau Voltage	Vplateau		-	5.2	-	V
Switching Characteristics						
Turn-On Delay Time	td(on)	VGS = 10V, VDS = 50V, ID = 100A RG = 6Ω	-	26	-	nS
Rise Time	tr		-	75	-	
Turn-Off Delay Time	td(off)		-	87	-	
Fall Time	tf		-	30	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	VSD	IS = 1A, VGS = 0V, TJ = 25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	180	A
Body Diode Reverse Recovery Time	Trr	IS = 100A, di/dt = 100A/us, TJ = 25℃	-	72	-	nS
Body Diode Reverse Recovery Charge	Qrr		-	180	-	nC

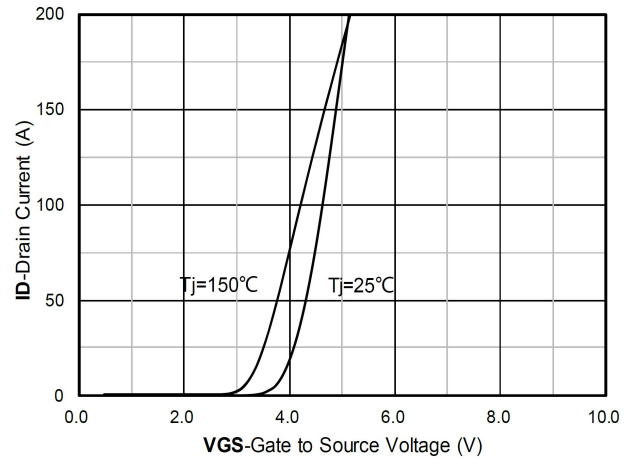
Note :

1. The test condition is VDD=50V, VGS=10V, L=0.5mH, RG=25 Ω

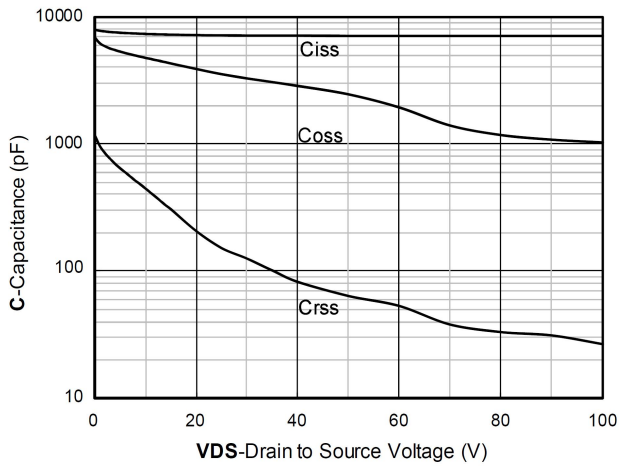
Typical Characteristics



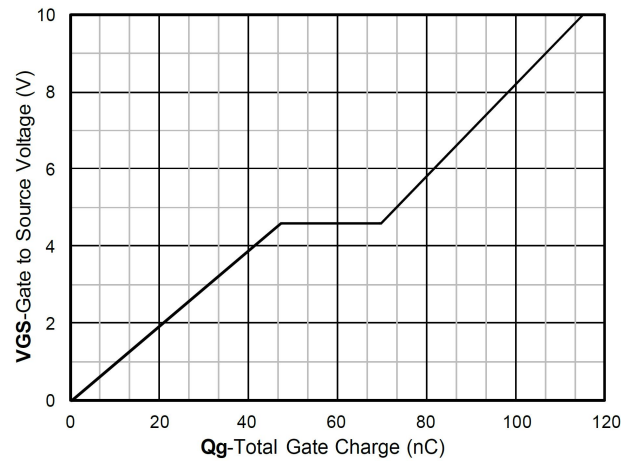
Output Characteristics



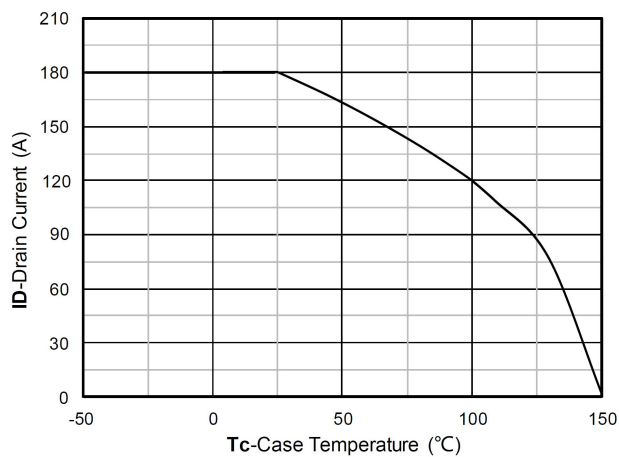
Transfer Characteristics



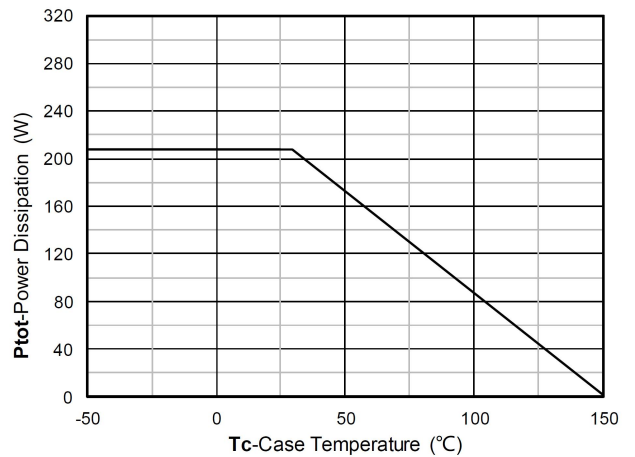
Capacitance Characteristics



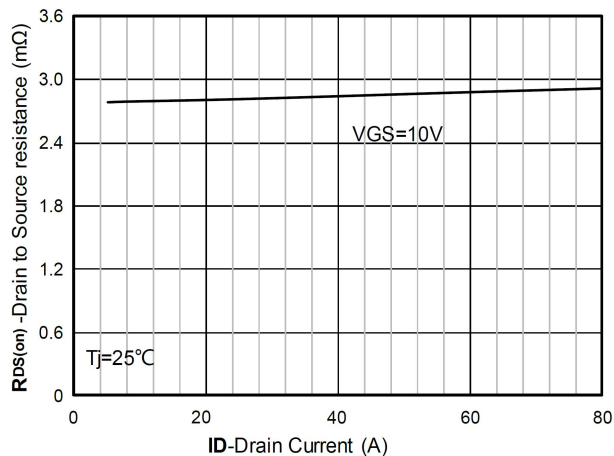
Gate Charge



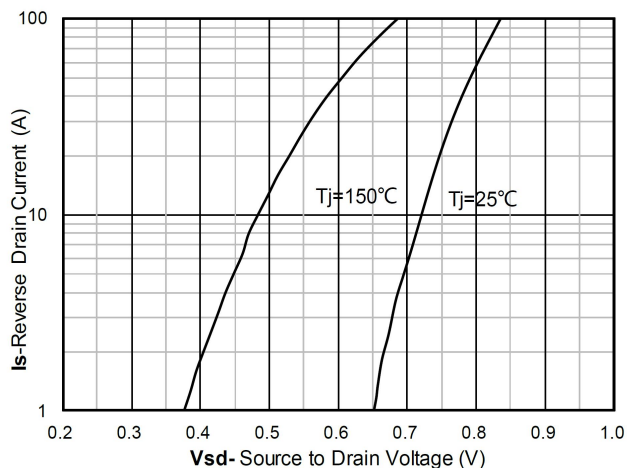
Current dissipation



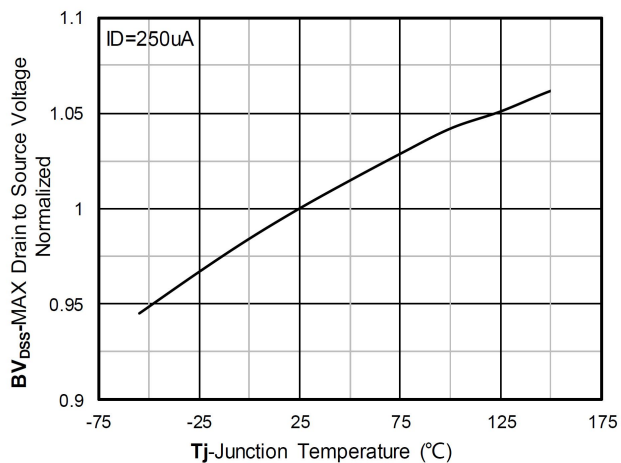
Power dissipation



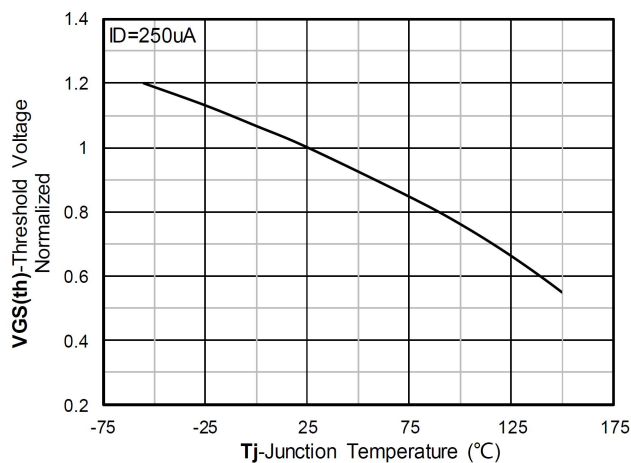
$R_{DS(on)}$ VS Drain Current



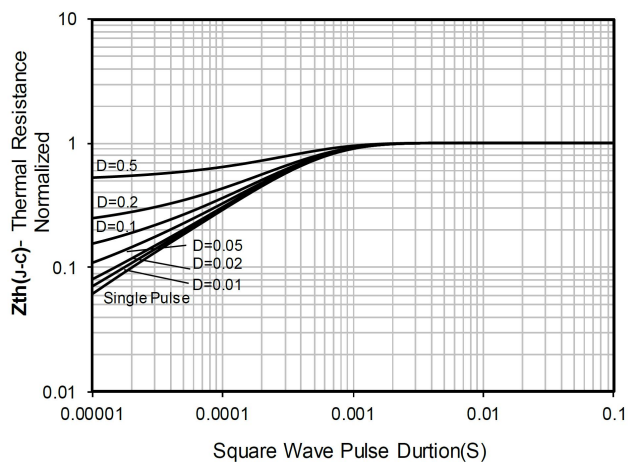
Forward characteristics of reverse diode



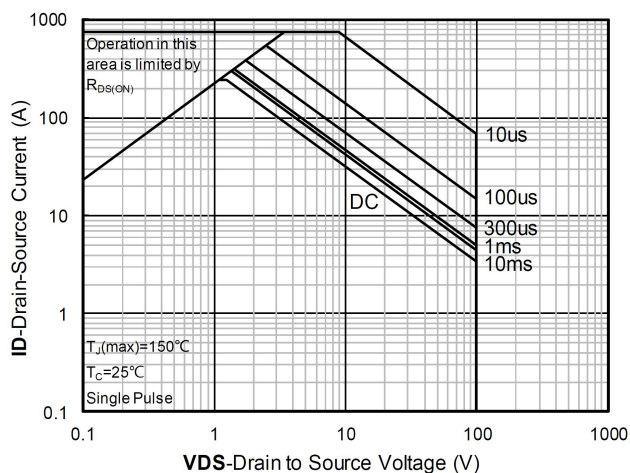
Normalized breakdown voltage



Normalized Threshold voltage



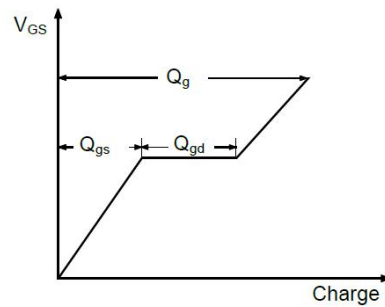
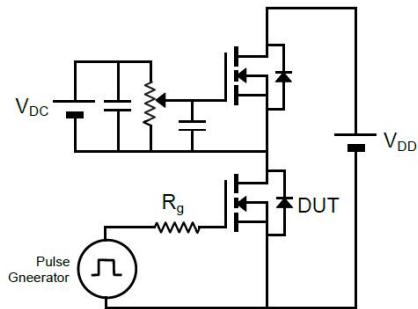
Maximum Transient Thermal Impedance



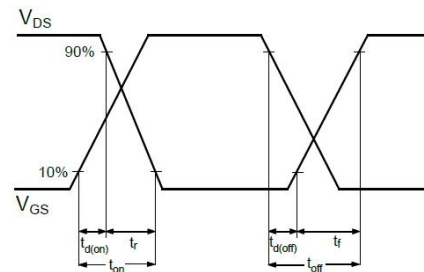
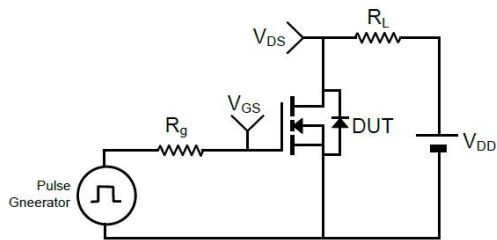
Safe Operation Area

Test Circuit

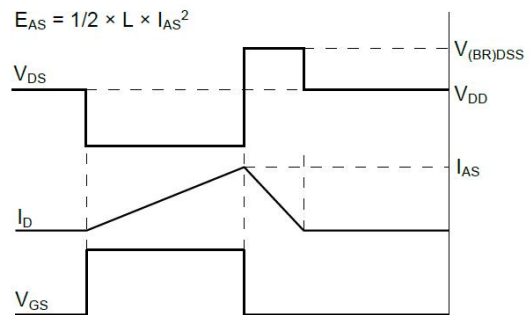
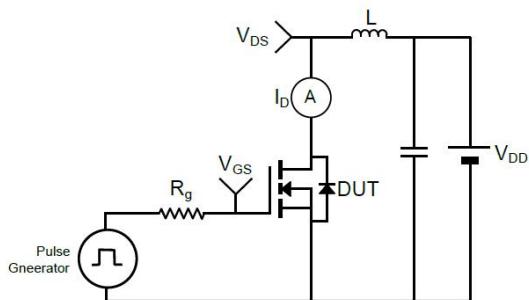
Gate Charge



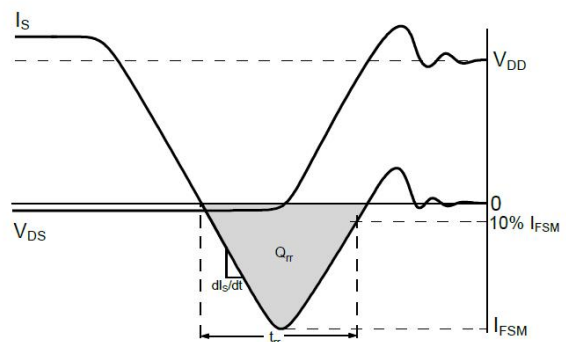
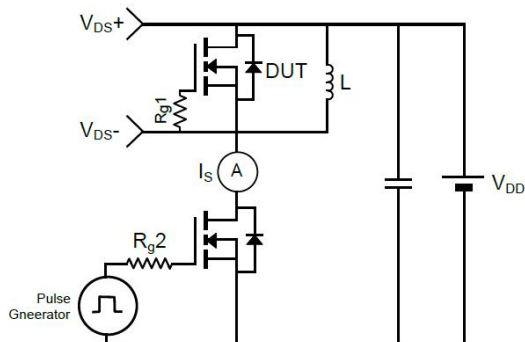
Resistive Load Switching Time



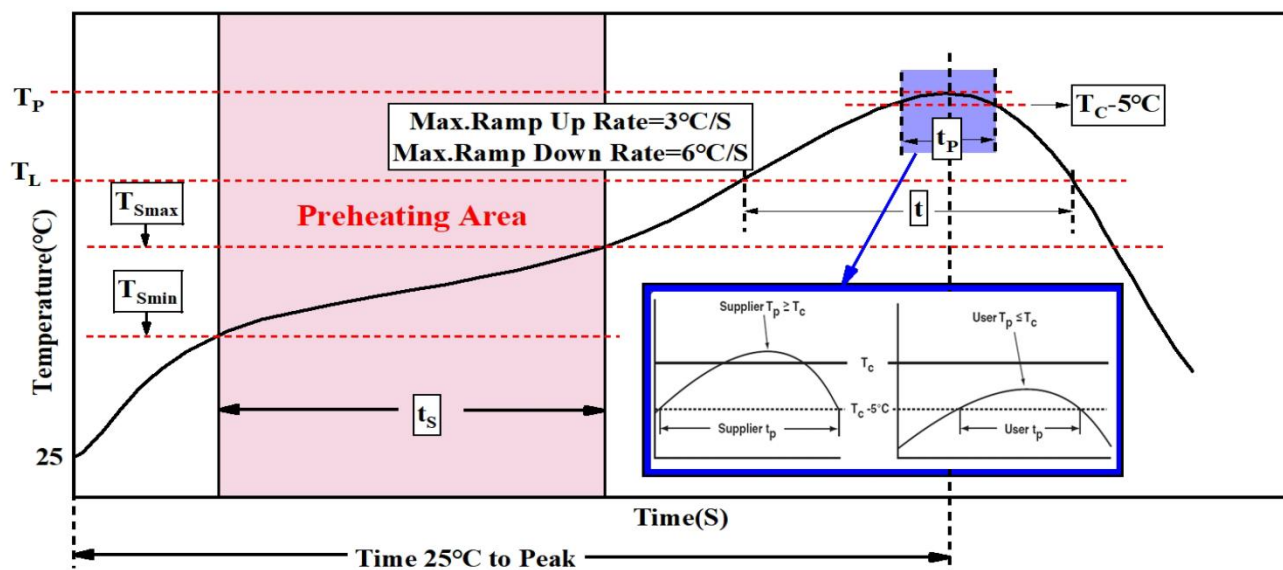
Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{Smin})	100°C	150°C
Temperature max (T_{Smax})	150°C	200°C
Time (T_{Smin} to T_{Smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{Smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217°C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_C)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{Smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_P) is defined as a supplier minimum and a user maximum		

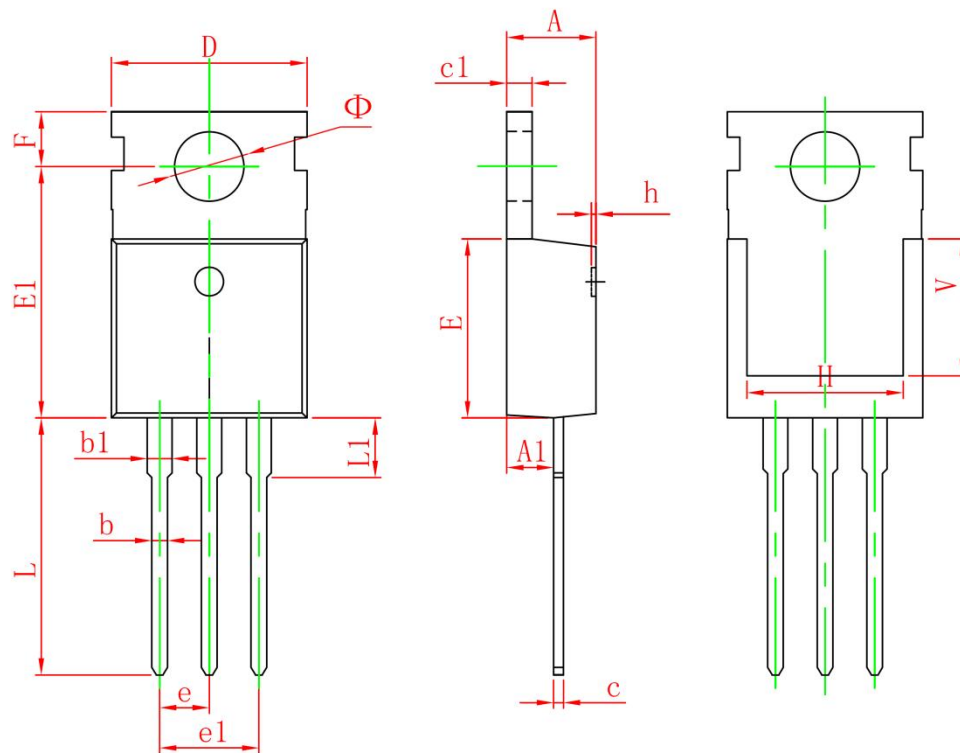
Table 1. SnPb Eutectic Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

TO-220-3L Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.300	4.700
A1	2.200	2.500
b	0.700	0.900
b1	1.100	1.400
c	0.300	0.700
c1	1.200	1.400
D	9.800	10.200
E	9.000	9.400
E1	12.700	13.500
e	2.490	2.590
e1	4.980	5.180
F	2.650	2.950
H	7.600	8.400
h	0.000	0.300
L	12.700	13.500
L1	2.850	3.250
V	6.900 REF.	
Φ	3.400	3.800